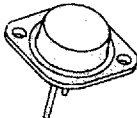


NEW ENGLAND SEMICONDUCTOR

BIPOLAR NPN TRANSISTOR TO-3

PACKAGE	DEVICE TYPE	V _{CEO} (sus) VOLTS	I _C (max) AMPS	h _{FE} @ I _C / V _{CE} (min/max @ A/V)	V _{CE(sat)} @ I _C /I _B (V @ A/A)	P _D * WATTS	f _T (MHz)
	NPN	40	6	15-45@1.5/4	3@1.5/3	75	1.0
	TO-3	55	6	15-45@1.5/4	3@1.5/3	75	1.0
	2N1487	40	6	25-75@1.5/4	1@1.5/1	75	1.0
	2N1488	55	6	25-75@1.5/4	1@1.5/1	75	1.0
	2N1489	55	6	20-70@4/4	1.1@4/4	115	2.5
	2N1490	60	10	25-90@1/2	1@5/5	150	2.5
	2N3055^	60	10	25-90@1/2	1@5/5	150	2.5
	2N3713	80	10	50-150@1/2	.8@5/5	150	2.5
	2N3714	60	10	50-150@1/2	.8@5/5	150	2.5
	2N3715^	40	30	15-60@15/4	2@15/1.5	150	0.2
	2N3716^	60	20	15-60@10/4	1.4@10/1	150	0.2
	2N3771	140	16	15-60@8/4	1.4@8/8	150	0.2
	2N3772	100	10	40-120@5/5	.6@5/5	115	20
	2N3773	150	10	40-120@5/5	.6@5/5	115	20
	2N4070	90	20	20-100@12/5	1@12/1.2	140	60 ^t
	2N4071	75	20	20-100@10/5	1@10/1	140	60 ^t
	2N5038^	90	30	20-100@15/2	.75@15/1.2	140	50
	2N5039^	120	30	20-100@15/2	.75@15/1.2	140	50
	2N5671^	60	50	15-60@25/2	1@25/2.5	300	2
	2N5672^	80	50	15-60@25/2	1@25/2.5	300	2
	2N5685^	80	30	20-100@10/4	2@10/.66	175	30
	2N5686^	120	30	20-100@10/4	2@10/.66	175	30
	2N5929	160	30	20-100@10/4	2@10/.66	175	30
	2N5930						
	2N5931						

* T_C = 25°C

^h V_{CER}

^t Typical

^Available in JAN, JANTX, JANTXV